

# NPN 5 GHz wideband transistor

# BFR92A

### FEATURES

- High power gain
- Low noise figure
- Low intermodulation distortion.

### APPLICATIONS

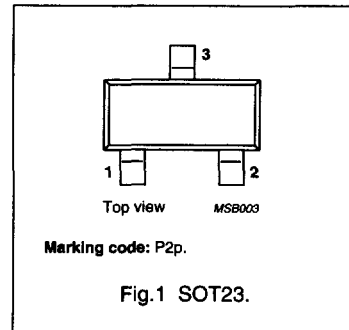
- RF wideband amplifiers and oscillators.

### DESCRIPTION

NPN wideband transistor in a plastic SOT23 package.  
PNP complement: BFT92.

### PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



### QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
$V_{CBO}$	collector-base voltage		–	20	V
$V_{CEO}$	collector-emitter voltage		–	15	V
$I_C$	collector current (DC)		–	25	mA
$P_{tot}$	total power dissipation	$T_s \leq 95\text{ }^\circ\text{C}$	–	300	mW
$C_{re}$	feedback capacitance	$I_C = I_c = 0; V_{CE} = 10\text{ V}; f = 1\text{ MHz}$	0.35	–	pF
$f_T$	transition frequency	$I_C = 15\text{ mA}; V_{CE} = 10\text{ V}; f = 500\text{ MHz}$	5	–	GHz
$G_{UM}$	maximum unilateral power gain	$I_C = 15\text{ mA}; V_{CE} = 10\text{ V}; f = 1\text{ GHz}; T_{amb} = 25\text{ }^\circ\text{C}$	14	–	dB
		$I_C = 15\text{ mA}; V_{CE} = 10\text{ V}; f = 2\text{ GHz}; T_{amb} = 25\text{ }^\circ\text{C}$	8	–	dB
F	noise figure	$I_C = 5\text{ mA}; V_{CE} = 10\text{ V}; f = 1\text{ GHz}; \Gamma_s = \Gamma_{opt}; T_{amb} = 25\text{ }^\circ\text{C}$	2.1	–	dB
$V_O$	output voltage	$d_{lm} = -60\text{ dB}; I_C = 14\text{ mA}; V_{CE} = 10\text{ V}; R_L = 75\text{ }\Omega; f_p + f_q - f_r = 793.25\text{ MHz}$	150	–	mV

### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{CBO}$	collector-base voltage	open emitter	–	20	V
$V_{CEO}$	collector-emitter voltage	open base	–	15	V
$V_{EBO}$	emitter-base voltage	open collector	–	2	V
$I_C$	collector current (DC)		–	25	mA
$P_{tot}$	total power dissipation	$T_s \leq 95\text{ }^\circ\text{C}$ ; note 1; see Fig.3	–	300	mW
$T_{stg}$	storage temperature		–65	+150	$^\circ\text{C}$
$T_j$	junction temperature		–	175	$^\circ\text{C}$

### Note

1.  $T_s$  is the temperature at the soldering point of the collector pin.

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## THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-s}$	thermal resistance from junction to soldering point	$T_s \leq 95\text{ °C}$ ; note 1	260	K/W

## Note

- $T_s$  is the temperature at the soldering point of the collector pin.

## CHARACTERISTICS

$T_j = 25\text{ °C}$  unless otherwise specified.

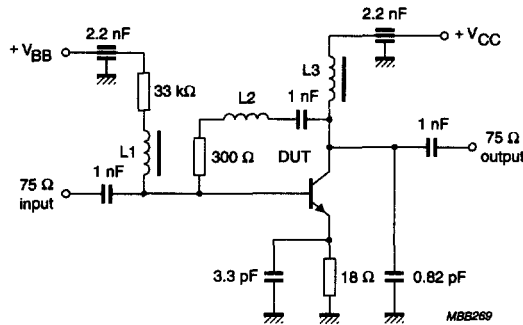
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$I_{CBO}$	collector leakage current	$I_E = 0$ ; $V_{CB} = 10\text{ V}$	–	–	50	nA
$h_{FE}$	DC current gain	$I_C = 15\text{ mA}$ ; $V_{CE} = 10\text{ V}$ ; see Fig.4	40	90	–	
$C_c$	collector capacitance	$I_E = I_B = 0$ ; $V_{CB} = 10\text{ V}$ ; $f = 1\text{ MHz}$ ; see Fig.5	–	0.6	–	pF
$C_e$	emitter capacitance	$I_C = I_C = 0$ ; $V_{EB} = 10\text{ V}$ ; $f = 1\text{ MHz}$	–	1.2	–	pF
$C_{re}$	feedback capacitance	$I_C = I_C = 0$ ; $V_{CE} = 10\text{ V}$ ; $f = 1\text{ MHz}$	–	0.35	–	pF
$f_T$	transition frequency	$I_C = 15\text{ mA}$ ; $V_{CE} = 10\text{ V}$ ; $f = 500\text{ MHz}$ ; see Fig.6	–	5	–	GHz
$G_{UM}$	maximum unilateral power gain (note 1)	$I_C = 15\text{ mA}$ ; $V_{CE} = 10\text{ V}$ ; $f = 1\text{ GHz}$ ; $T_{amb} = 25\text{ °C}$	–	14	–	dB
		$I_C = 15\text{ mA}$ ; $V_{CE} = 10\text{ V}$ ; $f = 2\text{ GHz}$ ; $T_{amb} = 25\text{ °C}$	–	8	–	dB
F	noise figure	$I_C = 5\text{ mA}$ ; $V_{CE} = 10\text{ V}$ ; $f = 1\text{ GHz}$ ; $\Gamma_s = \Gamma_{opt}$ ; $T_{amb} = 25\text{ °C}$ ; see Figs 13 and 14	–	2.1	–	dB
		$I_C = 5\text{ mA}$ ; $V_{CE} = 10\text{ V}$ ; $f = 2\text{ GHz}$ ; $\Gamma_s = \Gamma_{opt}$ ; $T_{amb} = 25\text{ °C}$ ; see Figs 13 and 14	–	3	–	dB
$V_O$	output voltage	notes 2 and 3	–	150	–	mV
$d_2$	second order intermodulation distortion	notes 2 and 4; see Fig.16	–	–50	–	dB

## Notes

- $G_{UM}$  is the maximum unilateral power gain, assuming  $S_{12}$  is zero and  $G_{UM} = 10 \log \frac{|S_{21}|^2}{(1 - |S_{11}|^2)(1 - |S_{22}|^2)} \text{ dB}$ .
- Measured on the same die in a SOT37 package (BFR90A).
- $d_{im} = -60\text{ dB}$  (DIN 45004B);  $I_C = 14\text{ mA}$ ;  $V_{CE} = 10\text{ V}$ ;  $R_L = 75\ \Omega$ ;  $V_{SWR} < 2$ ;  $T_{amb} = 25\text{ °C}$   
 $V_p = V_O$  at  $d_{im} = -60\text{ dB}$ ;  $f_p = 795.25\text{ MHz}$ ;  
 $V_q = V_O - 6\text{ dB}$ ;  $f_q = 803.25\text{ MHz}$ ;  
 $V_r = V_O - 6\text{ dB}$ ;  $f_r = 805.25\text{ MHz}$ ;  
measured at  $f_p + f_q - f_r = 793.25\text{ MHz}$ .
- $I_C = 14\text{ mA}$ ;  $V_{CE} = 10\text{ V}$ ;  $R_L = 75\ \Omega$ ;  $V_{SWR} < 2$ ;  $T_{amb} = 25\text{ °C}$   
 $V_p = 60\text{ mV}$  at  $f_p = 250\text{ MHz}$ ;  
 $V_q = 60\text{ mV}$  at  $f_q = 560\text{ MHz}$ ;  
measured at  $f_p + f_q = 810\text{ MHz}$ .

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L1 = L3 = 5 μH choke.  
 L2 = 3 turns 0.4 mm copper wire, internal diameter 3 mm, winding pitch 1 mm.

Fig.2 Intermodulation distortion and second harmonic distortion MATV test circuit.

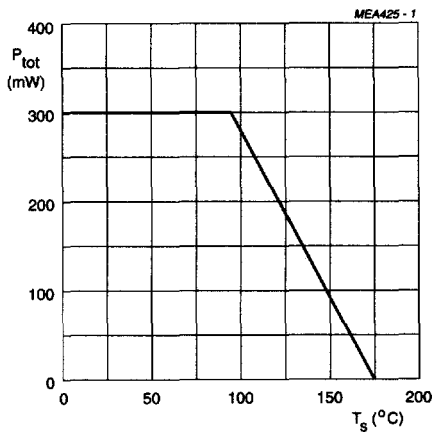
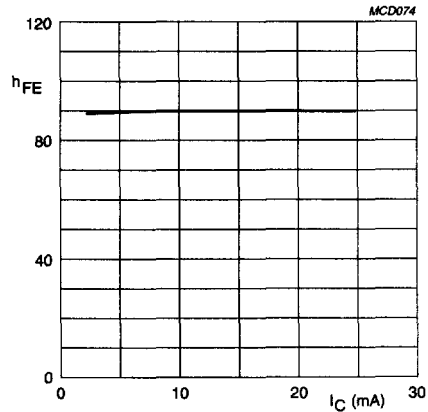


Fig.3 Power derating curve.

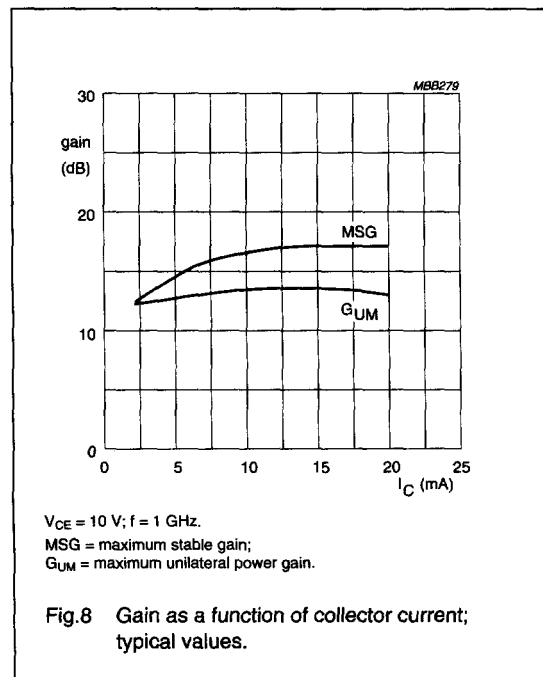
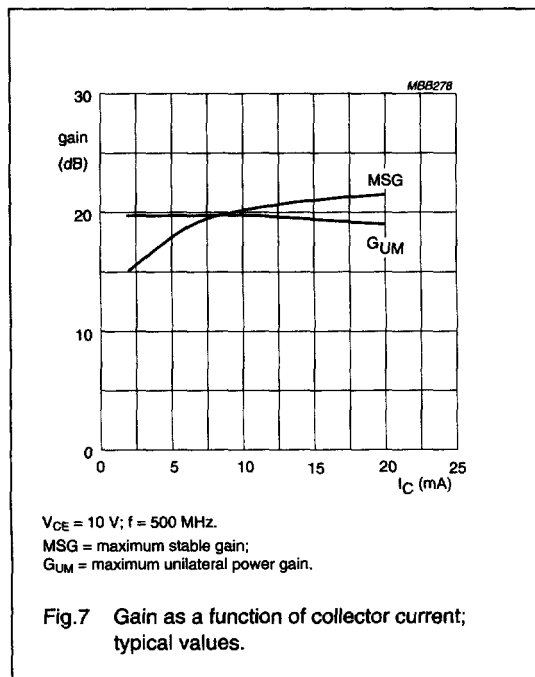
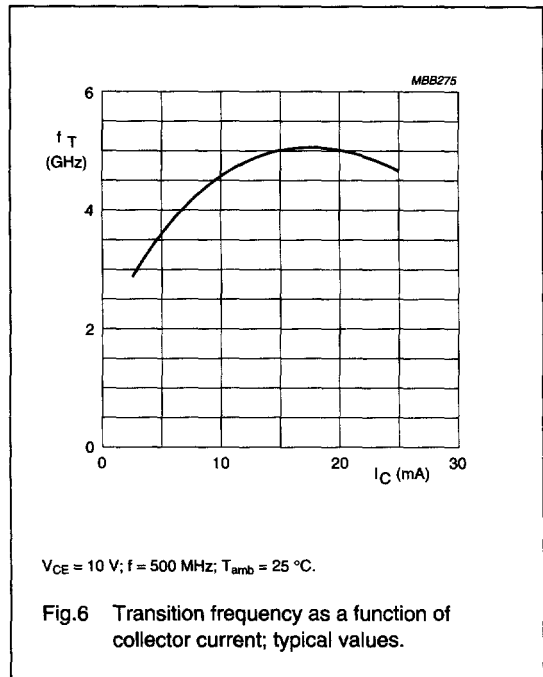
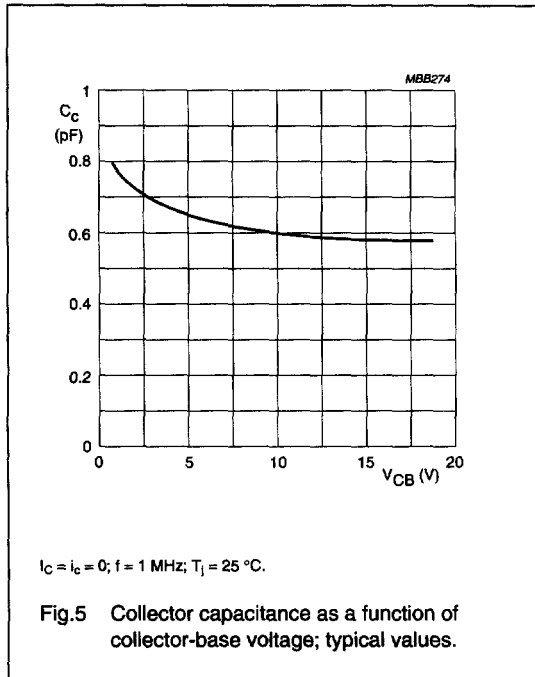


V<sub>CE</sub> = 10 V; T<sub>J</sub> = 25 °C.

Fig.4 DC current gain as a function of collector current; typical values.

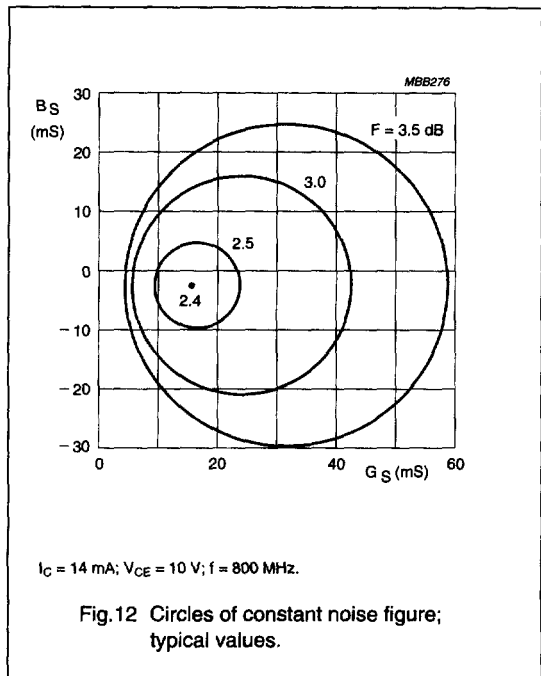
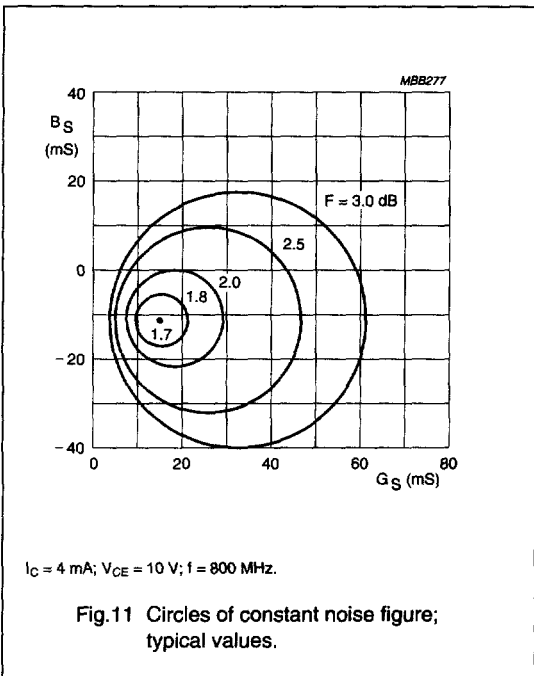
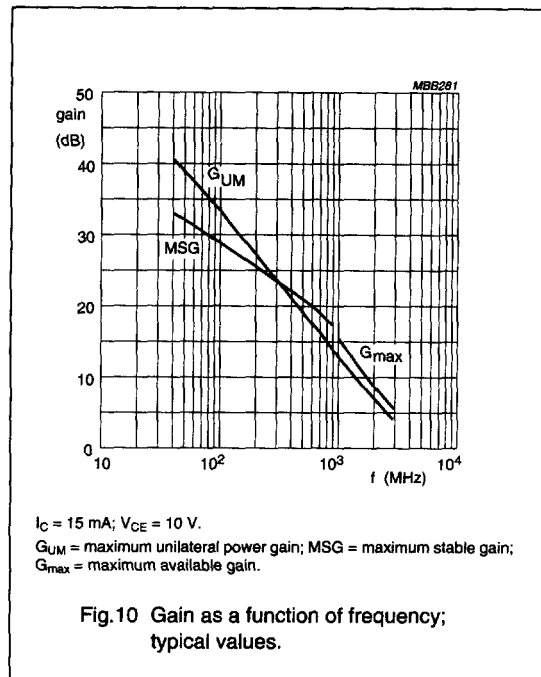
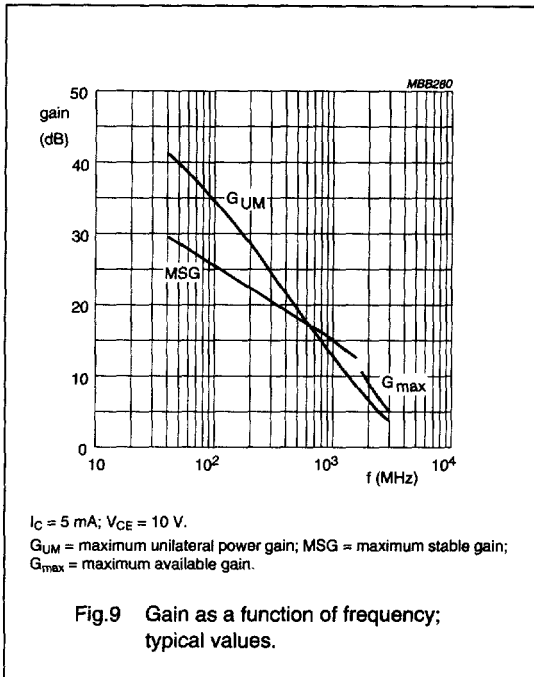
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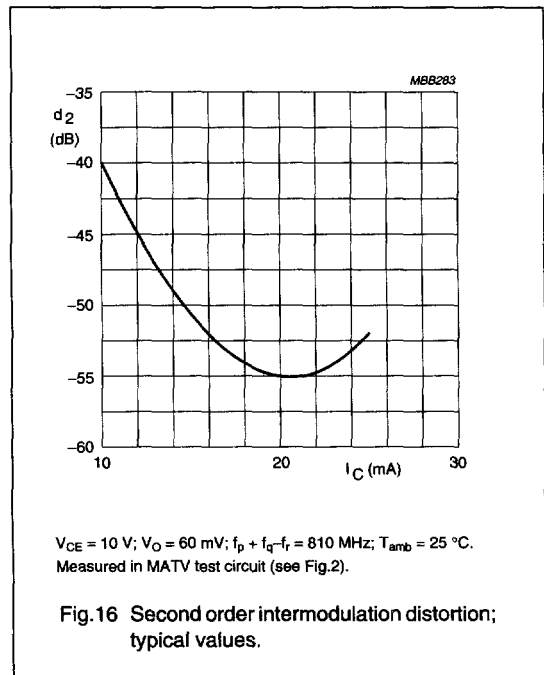
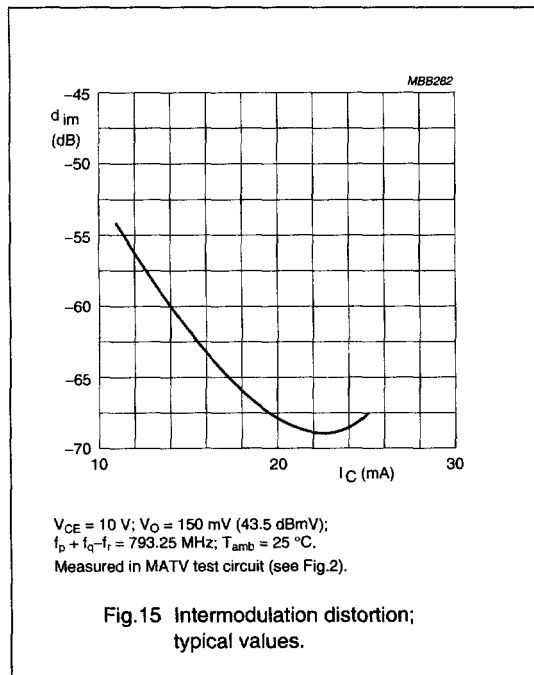
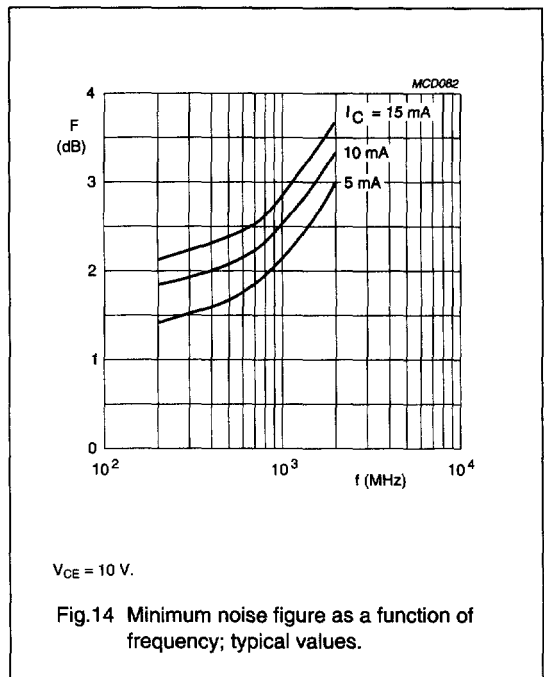
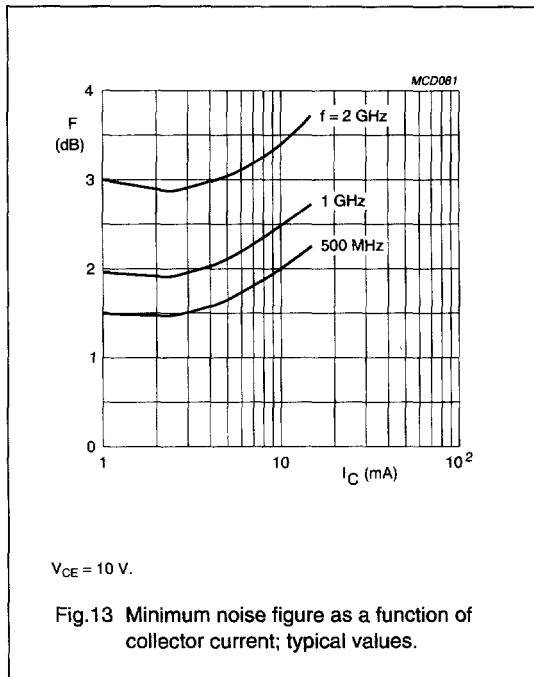
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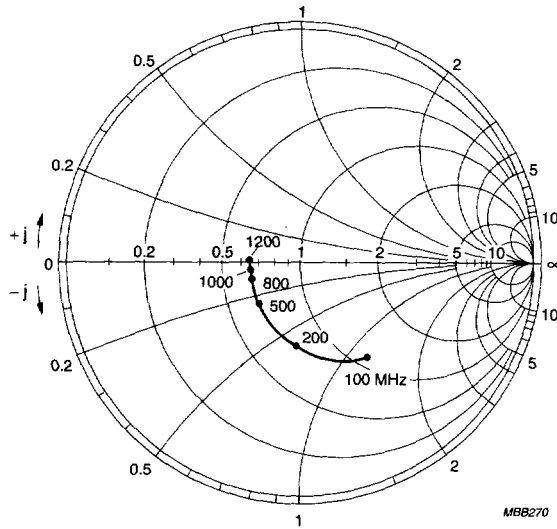
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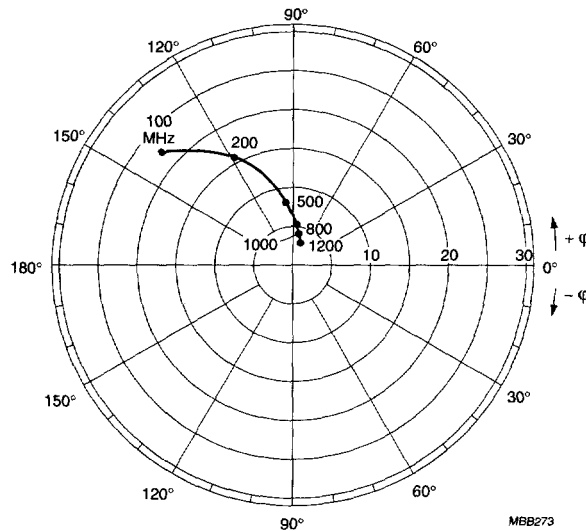
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$I_C = 14 \text{ mA}$ ;  $V_{CE} = 10 \text{ V}$ ;  $Z_0 = 50 \Omega$ ;  $T_{\text{amb}} = 25 \text{ }^\circ\text{C}$ .

Fig.17 Common emitter input reflection coefficient ( $S_{11}$ ); typical values.



$I_C = 14 \text{ mA}$ ;  $V_{CE} = 10 \text{ V}$ ;  $T_{\text{amb}} = 25 \text{ }^\circ\text{C}$ .

Fig.18 Common emitter forward transmission coefficient ( $S_{21}$ ); typical values.

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